

YTF151 Transistors

N-Channel Enhancement MOSFET

Military/High-Rel N

V(BR)DSS (V) 60.0

V(BR)GSS (V) 20.0

I(D) Max. (A) 40.0

I(DM) Max. (A) Pulsed I(D) 25.0

@Temp (°C) 100#

IDM Max (@25°C Amb) 160

@Pulse Width (s) (Condition)

Absolute Max. Power Diss. (W) 150

Minimum Operating Temp (°C) -55

Maximum Operating Temp (°C) 150

Thermal Resistance Junc-Case .83

Thermal Resistance Junc-Amb. 30

V(GS)th Max. (V) 4.0

V(GS)th (V) (Min) 2.0

@(VDS) (V) (Test Condition) 20.0

@I(D) (A) (Test Condition) 250u

I(DSS) Max. (A) 250u

@V(DS) (V) (Test Condition) 60.0

@Temp (°C) (Test Condition) 25

I(GSS) Max. (A) 100n